

Silicon Transistors

	Type No.	Case	Construction (see note 1)	Maximum Ratings at 25°C amb.			Characteristics					SPECIAL FEATURES				
				Interbase Voltage	I _E peak	P _{tot}	Intrinsic standoff ratio		Peak-current Emitter Current I _p at V _{B⁺B⁻} = 25 V	Interbase Resistance T _{BBO}						
							Min.	Max.		Min.	Max.					
				V	A	W			uA	kohm						
Silicon Unijunction	2N489	TO5	G	65	2	0.6	0.51	0.62	20	4.7	6.8					
	2N489A	TO5	G	65	2	0.6	0.51	0.62	15	4.7	6.8					
	2N489B	TO5	G	65	2	0.6	0.51	0.62	6	4.7	6.8					
	2N490	TO5	G	65	2	0.6	0.51	0.62	20	6.2	9.1					
	2N490A	TO5	G	65	2	0.6	0.51	0.62	15	6.2	9.1					
	2N490B	TO5	G	65	2	0.6	0.51	0.62	6	6.2	9.1					
	2N491	TO5	G	65	2	0.6	0.56	0.68	20	4.7	6.8					
	2N491A	TO5	G	65	2	0.6	0.56	0.68	15	4.7	6.8					
	2N491B	TO5	G	65	2	0.6	0.56	0.68	6	4.7	6.8					
	2N492	TO5	G	65	2	0.6	0.56	0.68	20	6.2	9.1					
	2N492A	TO5	G	65	2	0.6	0.56	0.68	15	6.2	9.1					
	2N492B	TO5	G	65	2	0.6	0.56	0.68	6	6.2	9.1					
	2N493	TO5	G	65	2	0.6	0.62	0.75	20	4.7	6.8					
	2N493A	TO5	G	65	2	0.6	0.62	0.75	15	4.7	6.8					
	2N493B	TO5	G	65	2	0.6	0.62	0.75	6	4.7	6.8					
	2N494	TO5	G	65	2	0.6	0.62	0.75	20	6.2	9.1					
	2N494A	TO5	G	65	2	0.6	0.62	0.75	15	6.2	9.1					
	2N494B	TO5	G	65	2	0.6	0.62	0.75	6	6.2	9.1					
	2N1671	TO5	G	35	2	0.45	0.47	0.62	25	4.7	9.1					
	2N1671A	TO5	G	35	2	0.45	0.47	0.62	25	4.7	9.1					
	2N1671B	TO5	G	35	2	0.45	0.47	0.62	6	4.7	9.1					
	2N2160	TO5	G	35	2	0.45	0.47	0.80	25	4.0	12.0					
	2N3980	TO18	P	35	1	0.36	0.68	0.82	2	4.0	8.0					
TIS43	SILECT	P	—	1	0.3	0.55	0.82	5	4.0	9.1						
PNP High Speed Choppers	3N108	TO72	PE	-50	-50	-50	0.02	0.3	-1.0	30	-1.0	50	-1.0	12	10	DUAL EMITTERS
	3N109	TO72	PE	-50	-50	-50	0.02	0.3	-1.0	150	-1.0	50	-1.0	12	10	
	3N110	TO72	PE	-50	-30	-30	0.02	0.3	-1.0	30	-1.0	50	-1.0	12	10	
	3N111	TO72	PE	-50	-30	-30	0.02	0.3	-1.0	150	-1.0	50	-1.0	12	10	
NPN High Speed Choppers	3N74	TO72	P	50	18	18	0.02	0.30	1.0	50	1.0	40	1.0	30	8	DUAL EMITTERS
	3N75	TO72	P	50	18	18	0.02	0.30	1.0	100	1.0	40	1.0	30	8	
	3N76	TO72	P	50	18	18	0.02	0.30	1.0	200	1.0	50	1.0	30	8	
	3N77	TO72	P	40	12	12	0.02	0.30	1.0	50	1.0	50	1.0	30	8	
	3N78	TO72	P	40	12	12	0.02	0.30	1.0	100	1.0	50	1.0	30	8	
	3N79	TO72	P	40	12	12	0.02	0.30	1.0	200	1.0	60	1.0	30	10	

NOTE 1: The following symbols have been used throughout the Product Summary:

Under "Construction":

- A — Alloyed
- D — Diffused
- E — Epitaxial
- G — Grown
- M — Mesa
- P — Planar

Under h_{FE}:

- * — h_{FE}

Under f_T:

- φ — f_{hfb}
- Δ — f_{hfe}
- ‡ — typical

Under Dissipation:

- † — dissipation at T_{case} = 25°C